Ryszard Korbutowicz

List of Publications by Year in descending order

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		2257263	2053342	
17	46	3	5	
papers	citations	h-index	g-index	
17	17	1 7	60	
17	17	17	68	
all docs	docs citations	times ranked	citing authors	

#	Article	IF	Citations
1	P-type Inversion at the Surface of \hat{l}^2 -Ga2O3 Epitaxial Layer Modified with Au Nanoparticles. Sensors, 2022, 22, 932.	2.1	3
2	Thermal synthesis of Ga2O3/SnO2 core–shell nanowires and their structural characterization. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2022, 282, 115743.	1.7	0
3	Thermal oxidation of [0001] GaN in water vapor compared with dry and wet oxidation: Oxide properties and impact on GaN. Applied Surface Science, 2022, 598, 153872.	3.1	4
4	Morphology of Ga2O3 Nanowires and Their Sensitivity to Volatile Organic Compounds. Nanomaterials, 2021, 11, 456.	1.9	17
5	Structural characterization of inkjet printed capacitor layers in various technological conditions. Soldering and Surface Mount Technology, 2020, 32, 235-240.	0.9	2
6	Inkjet Printed vs Screen Printed Microstrip Line on LTCC substrates. , 2019, , .		3
7	Synthesis and Characterization of Ga2O3 and In2O3 Nanowires. Advances in Electrical and Electronic Engineering, 2019, 17, .	0.2	0
8	Oxidation rates of aluminium nitride thin films: effect of composition of the atmosphere. Journal of Materials Science: Materials in Electronics, 2017, 28, 13937-13949.	1.1	9
9	Surface preparation for gallium nitride thick layers deposition by HVPE., 2009,,.		O
10	Wet thermal oxidation for GaAs, GaN and Metal/GaN device applications. , 2008, , .		7
11	Properties of GaN layers deposited on (0001) sapphire templates. , 2008, , .		1
12	Impact of the initial stage of deposition conditions on the properties of subsequent GaN Layer. , 2007, , .		0
13	Thick GaN Layers Deposited by Hydride Vapour Phase Epitaxy. , 2006, , .		0
14	Application of GaN laterally overgrown on sapphire. , 2001, , .		0
15	Optical properties of GaN layers grown by MOCVD. , 2001, 4413, 37.		0
16	<title>Photoreflectance and photoluminescence of InGaAs/GaAs structures</title> ., 1997, 3179, 125.		0
17	Photoreflectance spectroscopy of metalorganic chemical vapor deposition (MOCVD)-grown GaAs and GaAs/GaAlAs structures., 1995,,.		0